

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE : 6PT1803N1T**, 6KT1803N1T**

CHIP SIZE	0.80 * 0.80 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	23,580 pcs

Maximum Ratings(Ta=25°C)

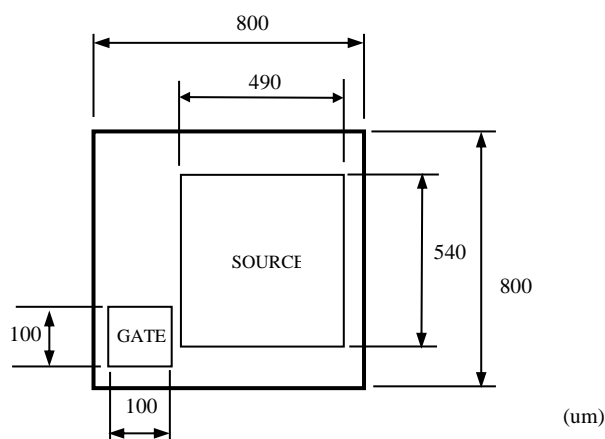
Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	30	V
Gate-source voltage	VGSS	±8	V
Drain Current (DC)	ID	2	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±2	uA	VGS=±8.0V VDS=0V
2	IDSS			500	nA	VDS=30V VGS=0V
3	BVDSS	33			V	ID=250uA
4	VTH	0.45		1.0	V	ID=250uA
5	Ron 1		0.05	0.08	Ω	ID=0.95A VGS=4.5V
6	Ron 2		0.07	0.11	Ω	ID=0.67A VGS=2.5V
7	Ron 3		0.12	0.21	Ω	ID=0.67A VGS=1.8V
8	VSD			0.9	V	IS=1A

※ Built-in ZD between Gate and Source.



NOTE: